



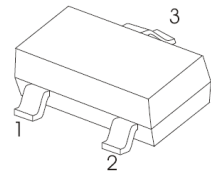
ShenzhenTaimaoTechnology Co.,Ltd.
SOT-23 Plastic-Encapsulate Diodes

BAP64-04,05,06 Pin Diode

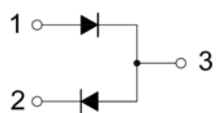
FEATURES

- High voltage ,current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- Low series inductance
- For applications up to 3 GHz

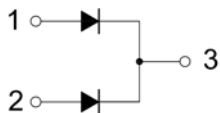
SOT-23



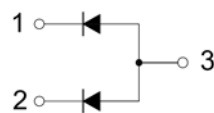
BAP64-04



BAP64-05



BAP64-06



MARKING:4K

MARKING:5K

MARKING:6K

Maximum Ratings (T_a=25°C unless otherwise specified)

Parameter	Symbol	Value	Units
Continuous reverse voltage	V _R	175	V
Continuous forward current	I _F	100	mA
Power dissipation	P _D	250	mW
Thermal resistance from junction to ambient	R _{θJA}	500	°C/W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~150	°C

Electrical characteristic (T_a=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward Voltage	V_F			1.1	V	I _F =50mA
Reverse Current	I_{R1}			10	μA	V _{R1} =175V
	I_{R2}			1		V _{R2} =20V
Diode Capacitance	C_{d1}		0.52		pF	V _R =0V, f=1MHz
	C_{d2}			0.5		V _R =1V, f=1MHz
	C_{d3}			0.35		V _R =20V, f=1MHz
Diode Forward Resistance (note 1)	R_{d1}			40	Ω	I _F =0.5mA, f=100MHz
	R_{d2}			20		I _F =1mA, f=100MHz
	R_{d3}			3.8		I _F =10mA, f=100MHz
	R_{d4}			1.35		I _F =100mA, f=100MHz
Charge Carrier Life Time	τ_L		1.55		μs	When switched from I _F =10mA to I _R =6mA; R _L =100Ω; measured at I _R =3mA
Series Inductance	L_S		1.4		nH	I _F =10mA, f=100MHz

Note:

1.Guaranteed on AQL basis: inspection level S4,AQL 1.0.